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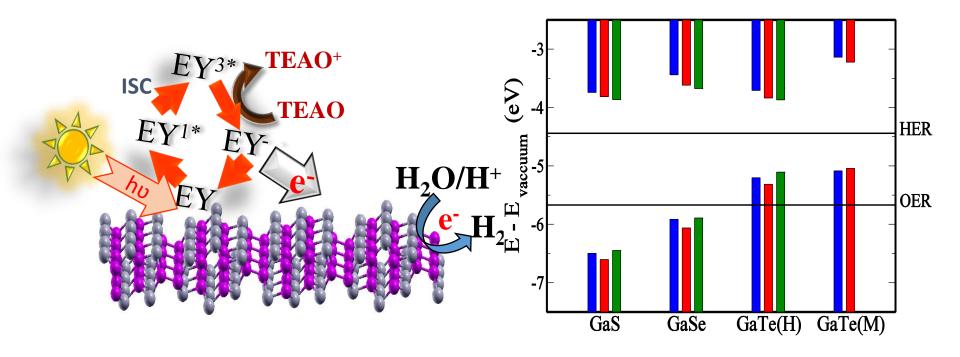
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Experimental and first-principles studies on hydrogen evolution properties of layered GaX (X=S,Se,Te)

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